



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ C$
40V	20m Ω @ $V_{GS} = 10V$	8.0A
	28m Ω @ $V_{GS} = 4.5V$	6.7A

Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

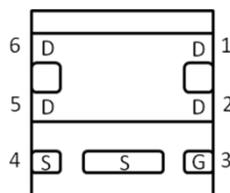
Mechanical Data

- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208⁽⁴⁾
- Weight: 0.0065 grams (Approximate)

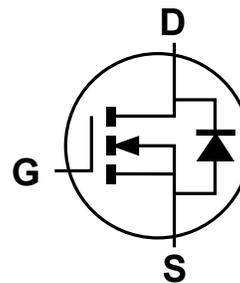
U-DFN2020-6 (Type E)



Bottom View



Pin Out



Equivalent Circuit

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	40	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	8.0 6.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	9.5 7.5	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	6.7 5.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	8.0 6.4	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	32	A
Maximum Body Diode Continuous Current			I_S	2.5	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	0.66	W
	$T_A = +70^\circ\text{C}$		0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	189	$^\circ\text{C/W}$
	$t < 10\text{s}$		132	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	P_D	2.03	W
	$T_A = +70^\circ\text{C}$		1.31	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	61	$^\circ\text{C/W}$
	$t < 10\text{s}$		43	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9.3	$^\circ\text{C}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	1	μA	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	—	2.4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	15	20	m Ω	$V_{GS} = 10\text{V}, I_D = 8\text{A}$
			20	28		$V_{GS} = 4.5\text{V}, I_D = 4\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1060	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	84	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	58	—	pF	
Gate Resistance	R_g	—	1.6	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	8.8	—	nC	$V_{DS} = 20\text{V}, I_D = 8\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	19.1	—	nC	
Gate-Source Charge	Q_{gs}	—	3.0	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.5	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.3	—	ns	$V_{DS} = 20\text{V}, R_L = 2.5\Omega$ $V_{GS} = 10\text{V}, R_G = 3\Omega$
Turn-On Rise Time	t_R	—	7.1	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	15.1	—	ns	
Turn-Off Fall Time	t_F	—	4.8	—	ns	
Reverse Recovery Time	t_{RR}	—	10.5	—	ns	$I_F = 8\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	4.15	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

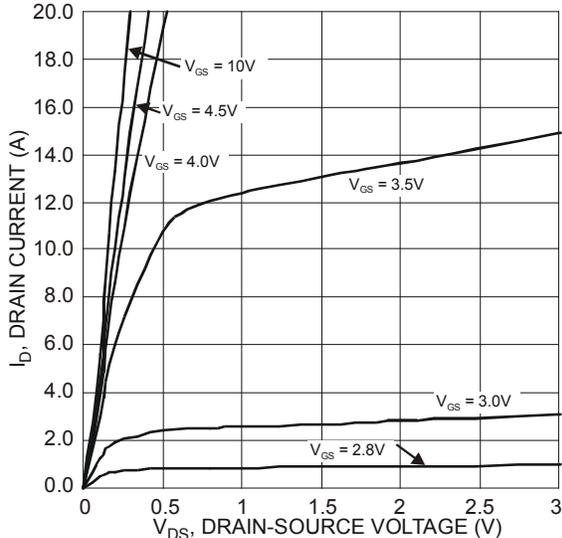


Figure 1 Typical Output Characteristic

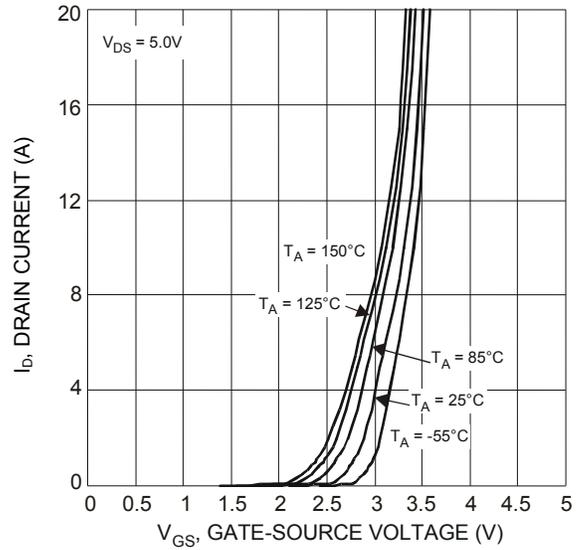


Figure 2 Typical Transfer Characteristics

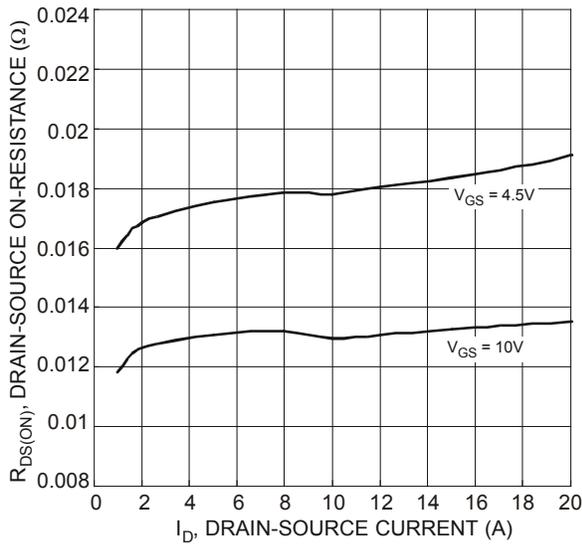


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

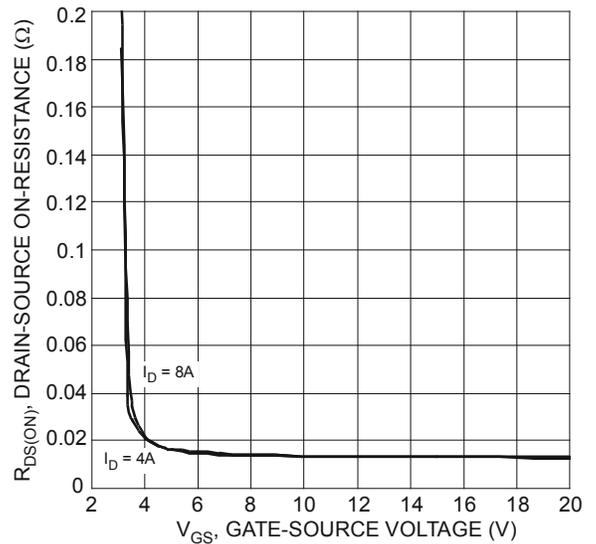


Figure 4 Typical Transfer Characteristics

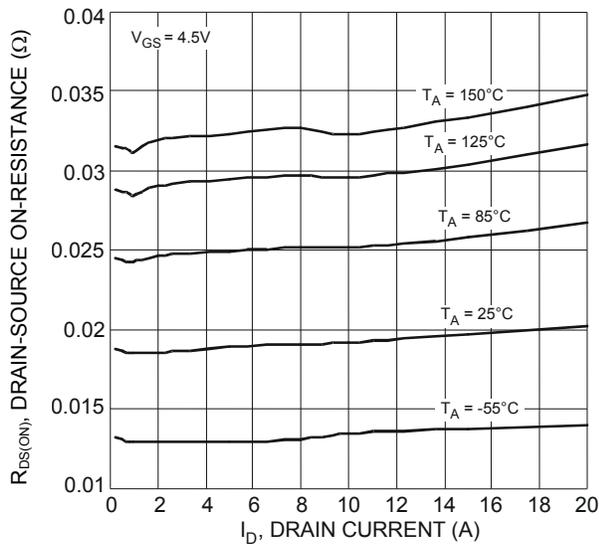


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

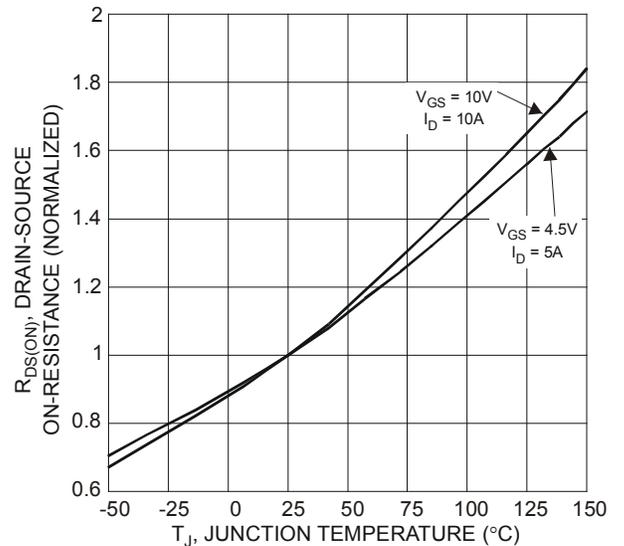


Figure 6 On-Resistance Variation with Temperature

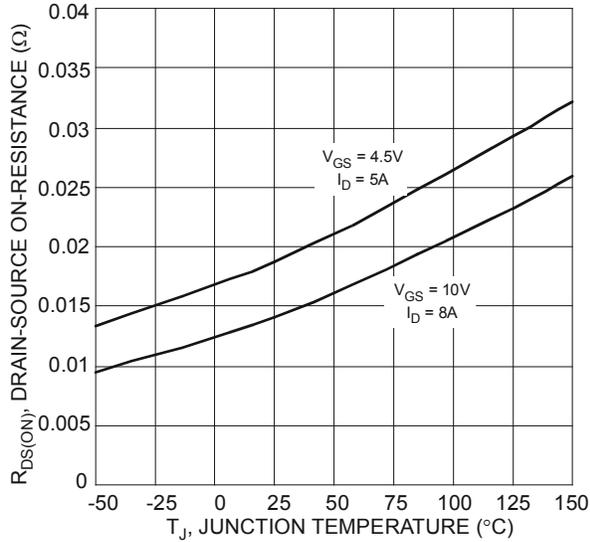


Figure 7 On-Resistance Variation with Temperature

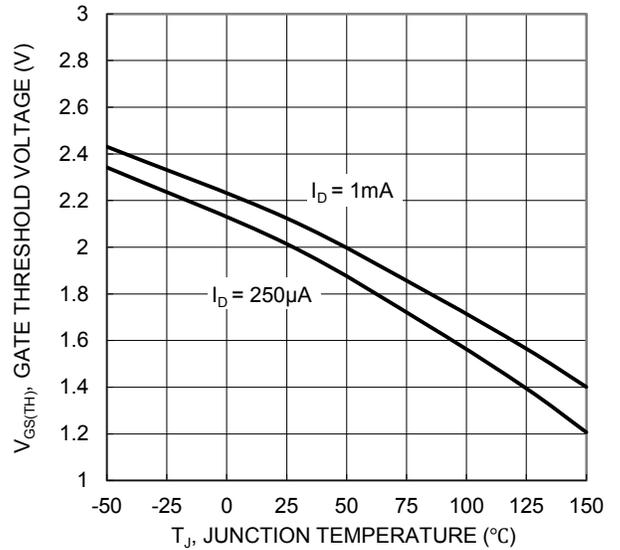


Figure 8 Gate Threshold Variation vs Temperature

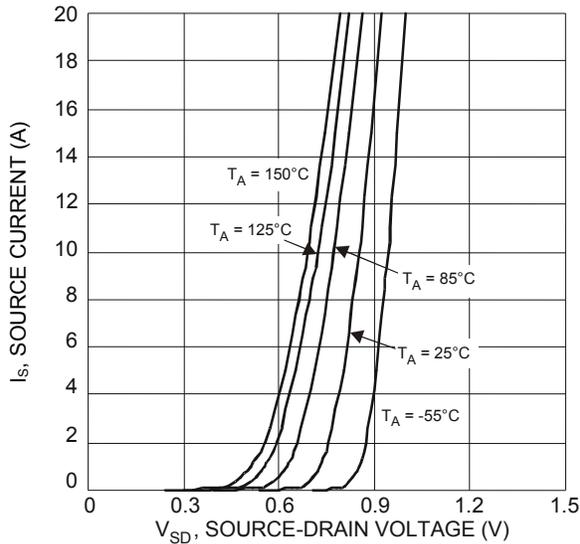


Figure 9 Diode Forward Voltage vs. Current

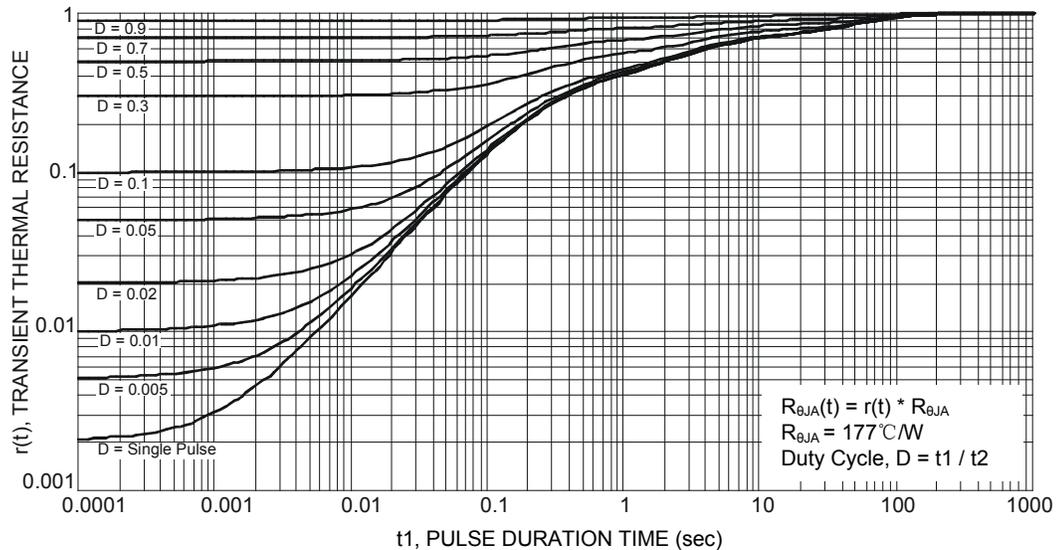
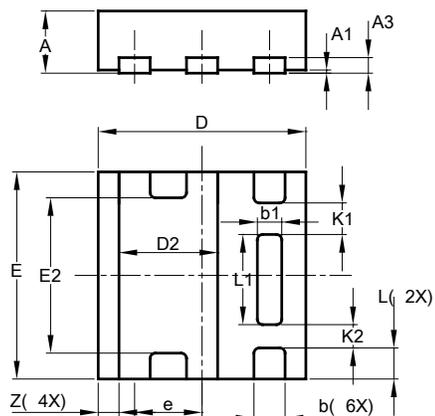


Figure 10 Transient Thermal Resistance

Package Outline Dimensions

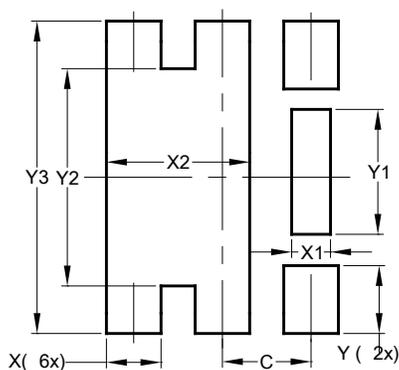
U-DFN2020-6 (Type E)



U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	–	–	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	–	–	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	–	–	0.305
K2	–	–	0.225
Z	–	–	0.20
All Dimensions in mm			

Suggested Pad Layout

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300